

Features

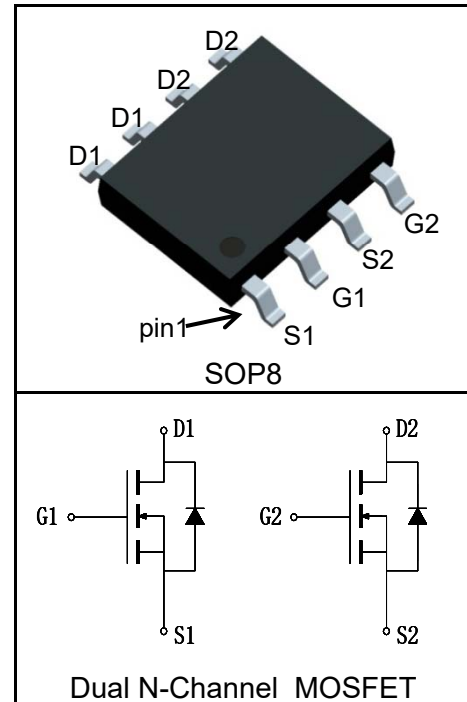
- 40V/10A,
 $R_{DS(ON)} = 11m\Omega(Typ.)@V_{GS}=10V$
 $R_{DS(ON)} = 17m\Omega(Typ.)@V_{GS}=4.5V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged

Applications

- Power Management



Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^\circ C$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	40	V
V_{GSS}	Gate-Source Voltage	± 20	
T_J	Maximum Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
I_S	Diode Continuous Forward Current	$T_A=25^\circ C$ 2.5	A
Mounted on Large Heat Sink			
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_A=25^\circ C$ 40	A
$I_D^{②}$	Continuous Drain Current($V_{GS}=10V$)	$T_A=25^\circ C$ 10	A
		$T_A=70^\circ C$ 8	
P_D	Maximum Power Dissipation	$T_A=25^\circ C$ 2	W
		$T_A=70^\circ C$ 1.3	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	-	$^\circ C/W$
$R_{\theta JA}^{③}$	Thermal Resistance-Junction to Ambient	62.5	$^\circ C/W$
Drain-Source Avalanche Ratings			
$E_{AS}^{④}$	Avalanche Energy, Single Pulsed	25	mJ

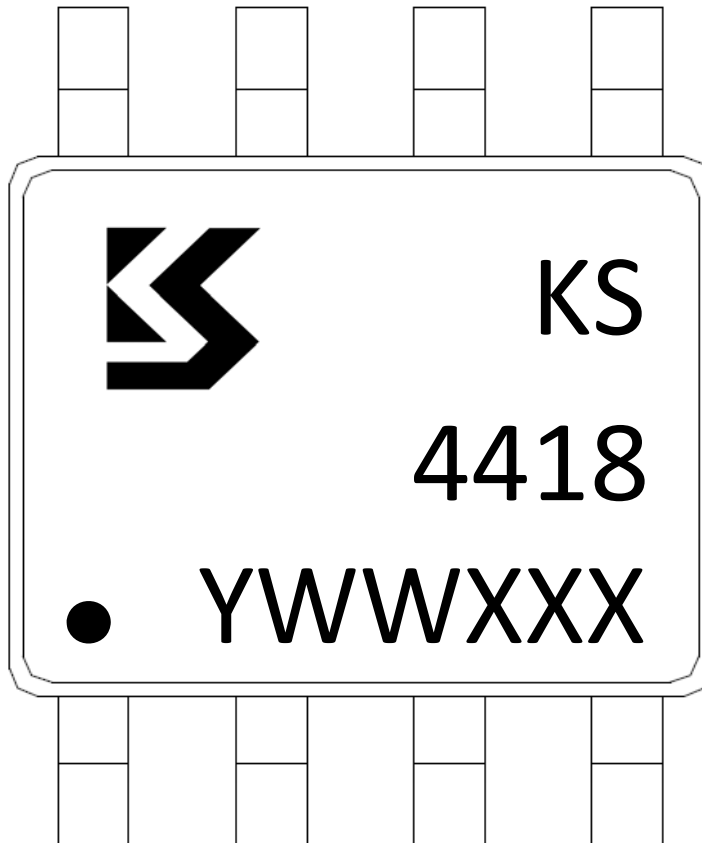
Electrical Characteristics ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KS4418HA			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	40			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=40V, V_{GS}=0V$			1	μA
		$T_J=125^\circ C$			30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1.3	1.8	2.3	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(5)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=10A$		11	14	$m\Omega$
		$V_{GS}=4.5V, I_{DS}=6A$		17	22	$m\Omega$
Diode Characteristics						
$V_{SD}^{(5)}$	Diode Forward Voltage	$I_{SD}=10A, V_{GS}=0V$		0.8	1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=10A, di_{SD}/dt=100A/\mu s$		9		ns
Q_{rr}	Reverse Recovery Charge			8		nC
Dynamic Characteristics ⁽⁶⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$		1.7		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=20V,$ Frequency=1.0MHz		1315		pF
C_{oss}	Output Capacitance			100		
C_{rss}	Reverse Transfer Capacitance			80		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=20V, I_{DS}=10A,$ $V_{GEN}=10V, R_G=6\Omega$		8		ns
t_r	Turn-on Rise Time			4		
$t_{d(OFF)}$	Turn-off Delay Time			24		
t_f	Turn-off Fall Time			6		
Gate Charge Characteristics ⁽⁶⁾						
Q_g	Total Gate Charge	$V_{DS}=20V, V_{GS}=10V,$ $I_{DS}=10A$		22		nC
Q_{gs}	Gate-Source Charge			4.5		
Q_{gd}	Gate-Drain Charge			4.2		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10$ sec. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} , starting $T_J = 25^\circ C, L = 0.5mH, R_G = 25\Omega, I_{AS} = 10A, V_{GS} = 10V$.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

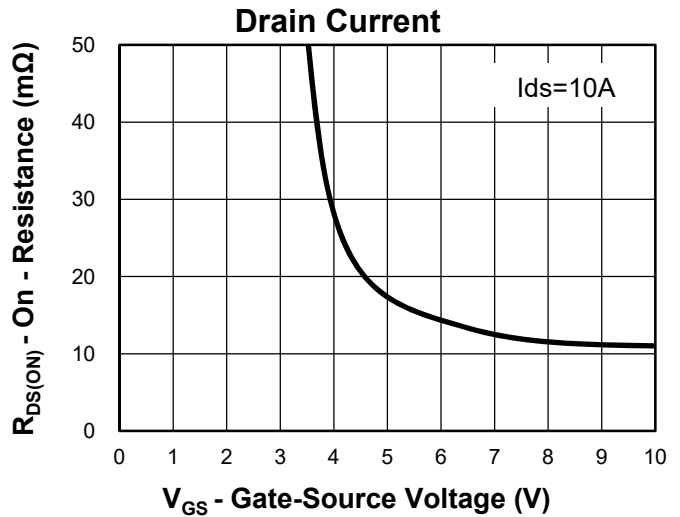
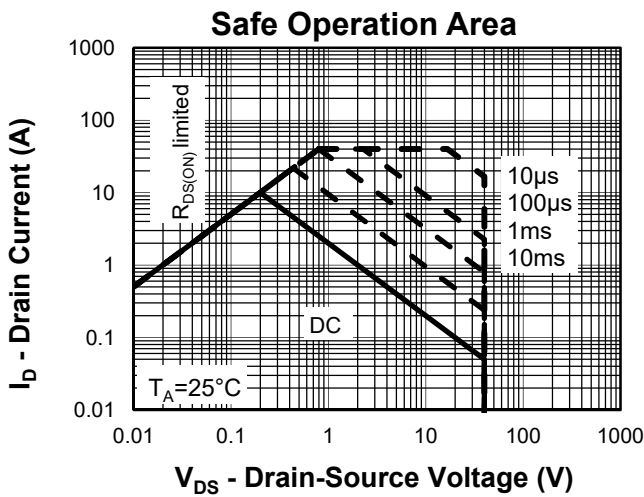
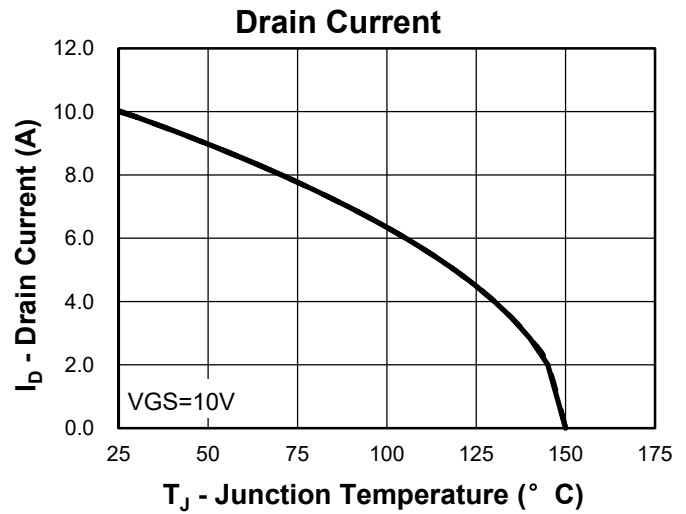
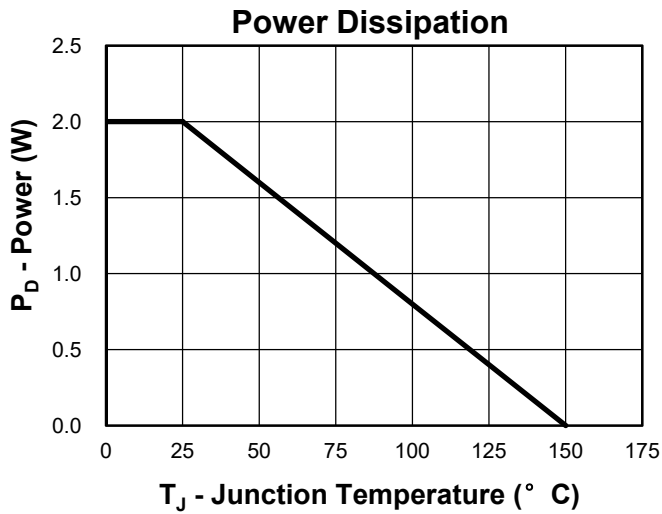
Ordering and Marking Information

Device	Package	Packaging	Quantity	Reel Size	Tape width
KS4418HA	SOP8	Tape&Reel	3000	13"	12mm

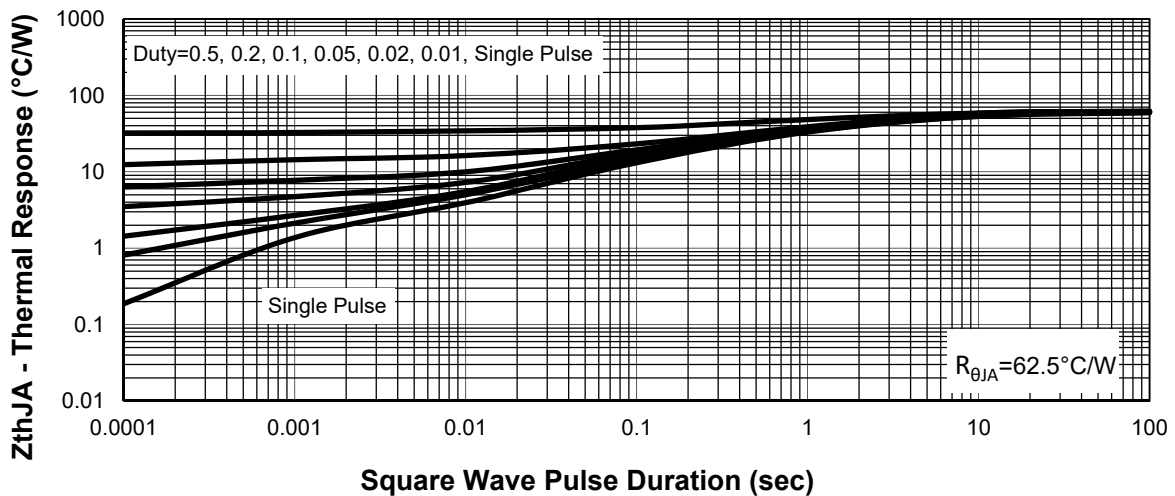


Y =Year,2017-A,2018-B,etc.
WW =Week.
XXX =Lot number.

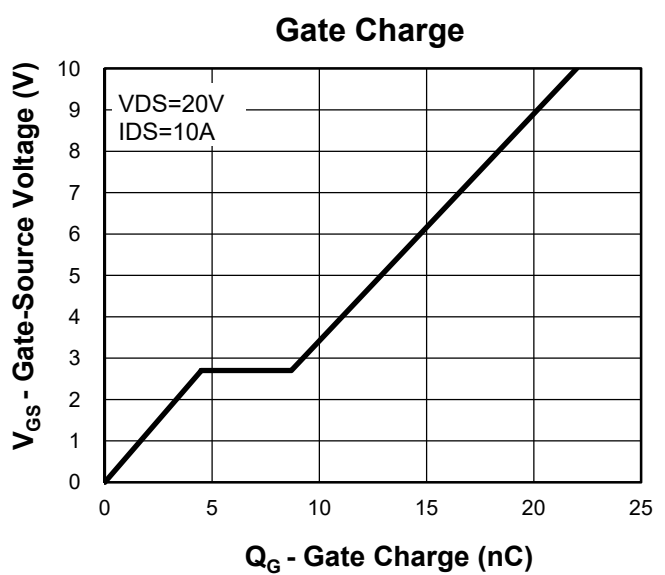
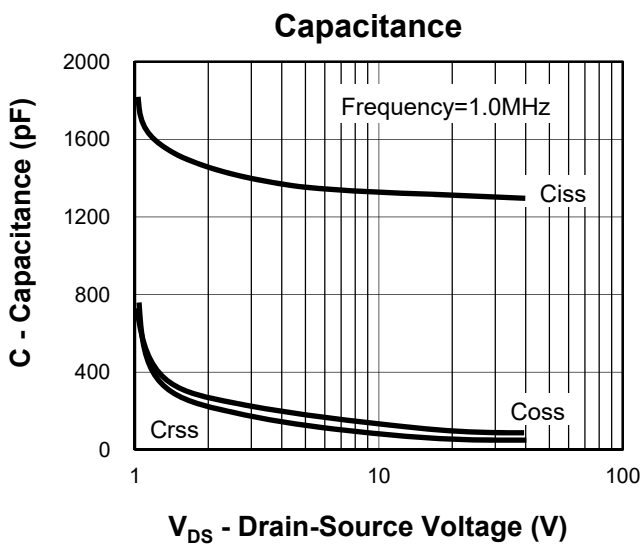
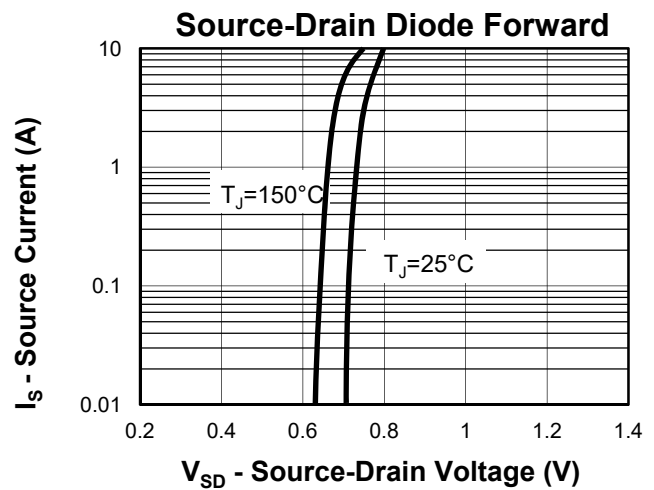
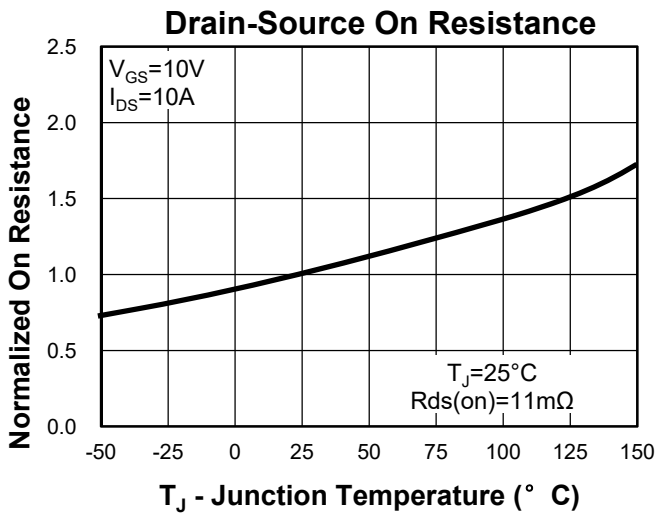
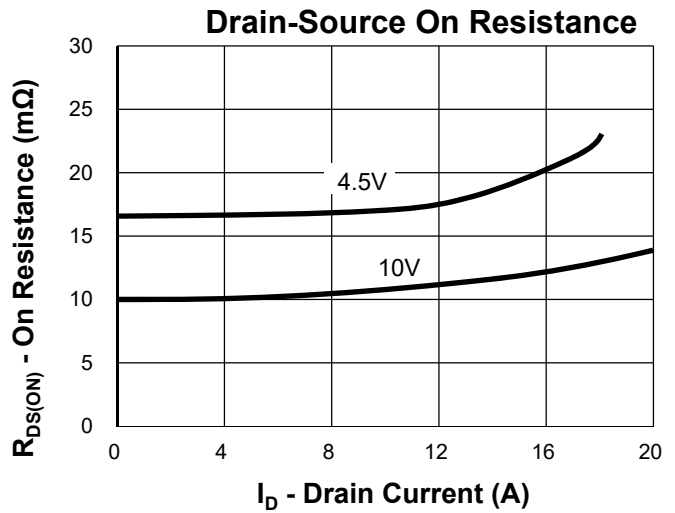
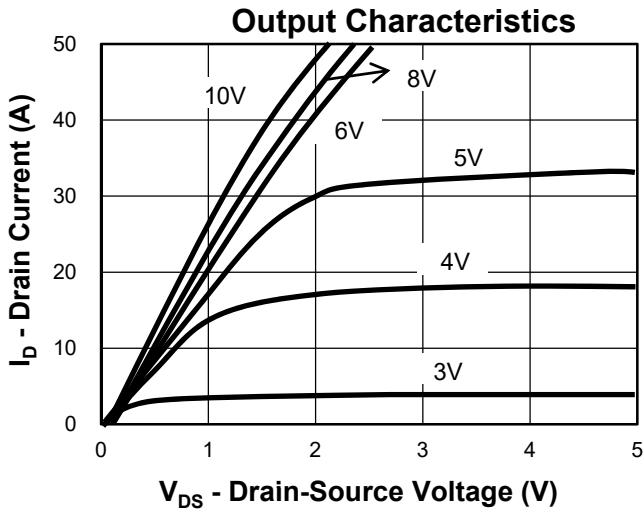
Typical Characteristics

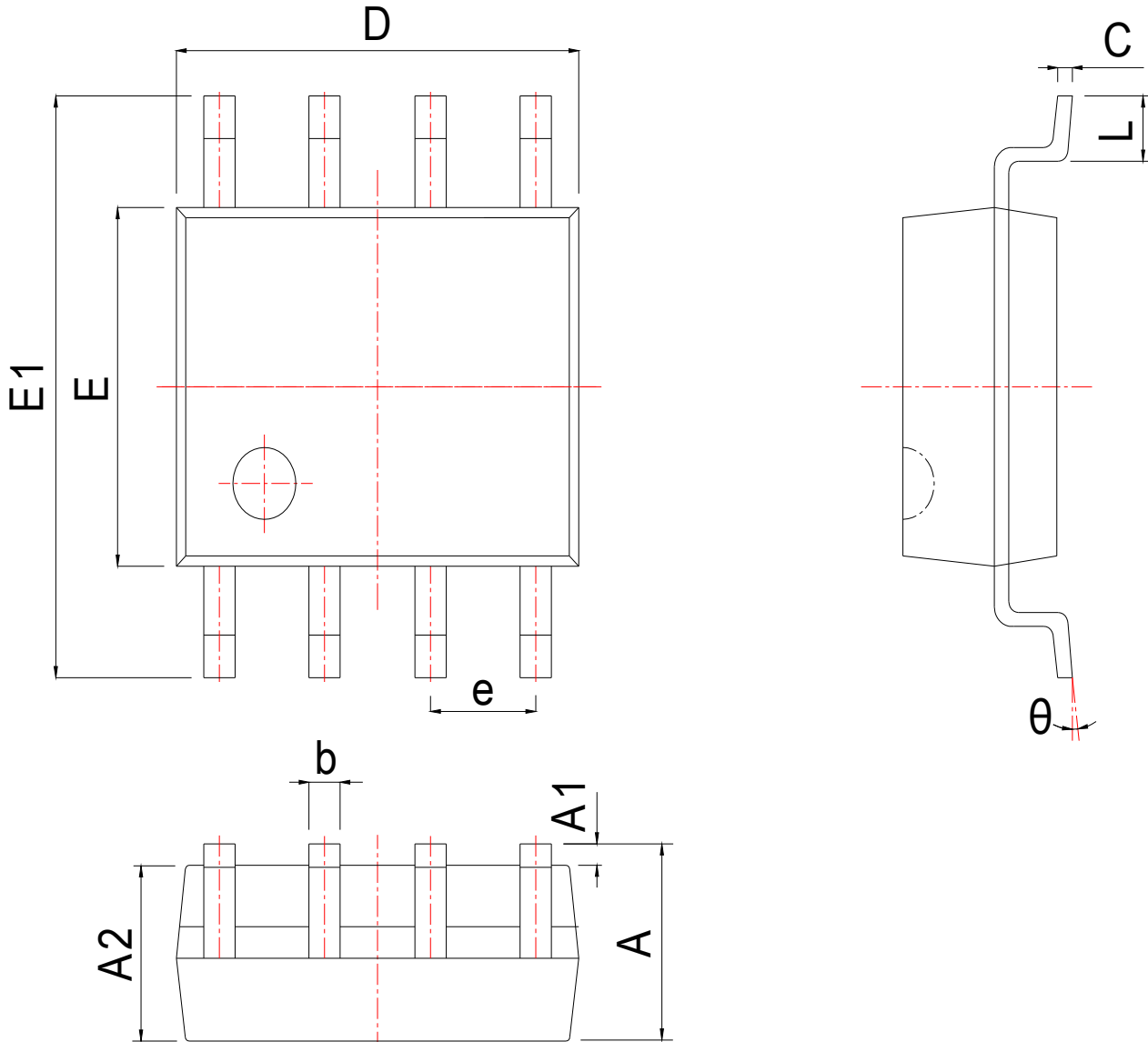


Thermal Transient Impedance



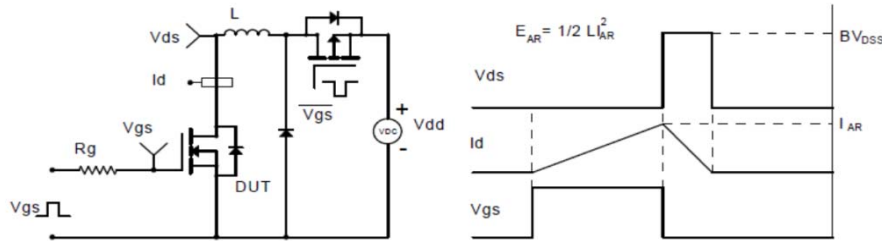
Typical Characteristics



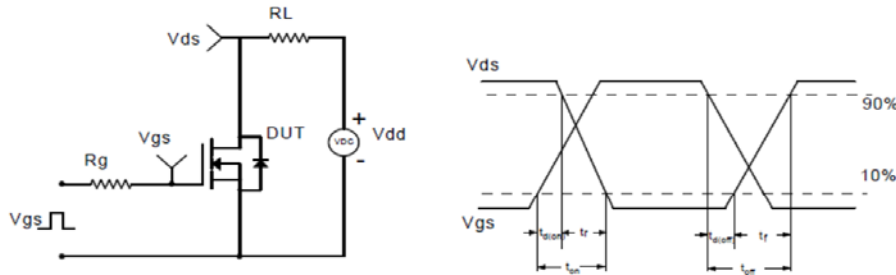
Package Information
SOP8


SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.300	1.525	1.750	0.051	0.060	0.069
A1	0.050	0.150	0.250	0.002	0.006	0.010
A2	1.350	1.450	1.550	0.053	0.057	0.061
b	0.330	0.420	0.510	0.013	0.017	0.020
c	0.170	0.210	0.250	0.007	0.008	0.010
D	4.700	4.900	5.100	0.185	0.193	0.201
E	3.800	3.900	4.000	0.150	0.154	0.157
E1	5.800	6.000	6.200	0.228	0.236	0.244
e	1.270 BSC			0.050 BSC		
L	0.400	0.835	1.270	0.016	0.033	0.050
θ	0°		8°	0°		8°

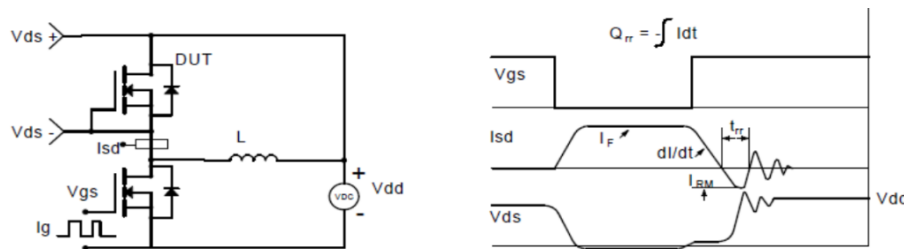
Avalanche Test Circuit and Waveforms



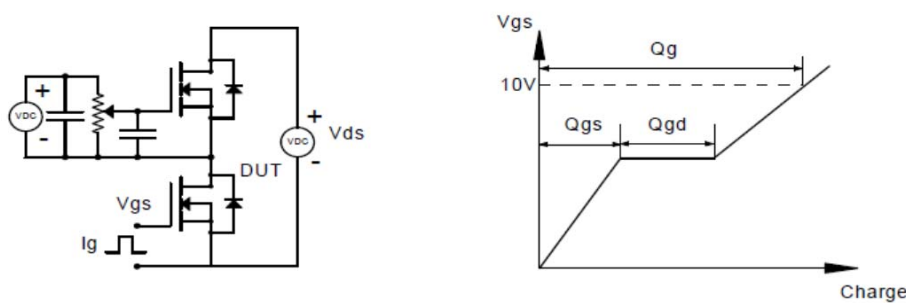
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

Kwansemi Semiconductor Co.,Ltd

Email:Sales@kwansemi.com

Web:www.kwansemi.com

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